

**1N6817**  
**(MSASC25W100K)**  
**1N6817R**  
**(MSASC25W100KR)**

**100 Volts**  
**25 Amps**

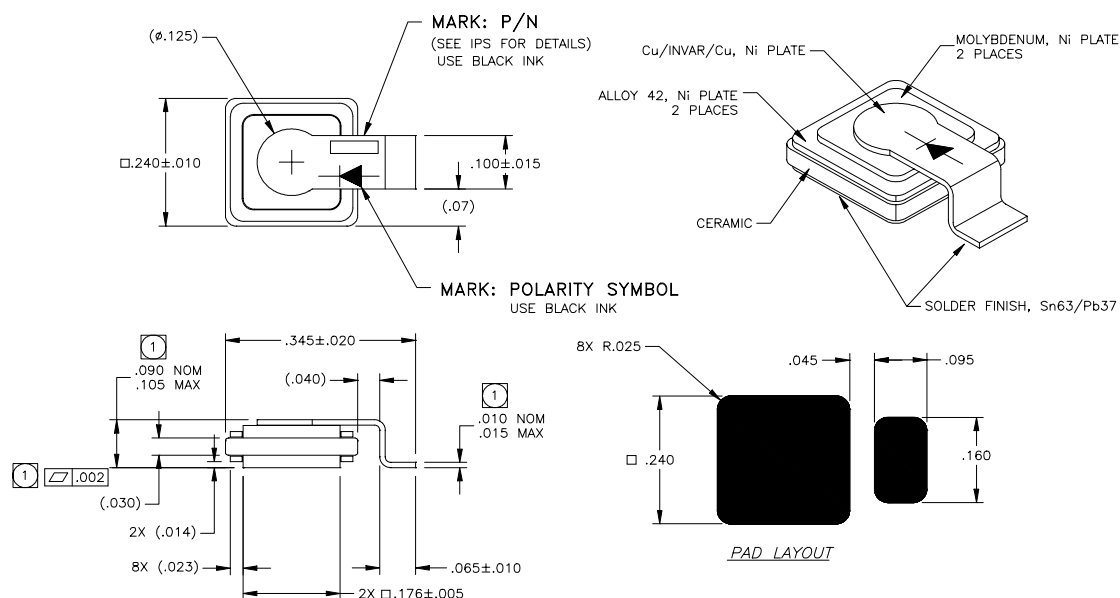
**LOW REVERSE**  
**LEAKAGE**  
**SCHOTTKY DIODE**

**Features**

- Tungsten schottky barrier
- Oxide passivated structure
- Guard ring protection for increased reverse energy capability
- Epitaxial structure minimizes forward voltage drop
- Hermetically sealed, low profile ceramic surface mount power package
- Low package inductance
- Very low thermal resistance
- Available as standard polarity (strap is anode: 1N6817) and reverse polarity (strap is cathode: 1N6817R)
- TXV-level screening (MSASC25W100KV) or S-level (MSASC25W100KS) screening i.a.w. Microsemi internal procedure PS11.50 available

**Maximum Ratings @ 25°C (unless otherwise specified)**

DESCRIPTION	SYMBOL	MAX.	UNIT
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	Volts
Working Peak Reverse Voltage	$V_{RWM}$	100	Volts
DC Blocking Voltage	$V_R$	100	Volts
Average Rectified Forward Current, $T_c \leq 145^\circ\text{C}$	$I_{F(ave)}$	25	Amps
derating, forward current, $T_c \geq 145^\circ\text{C}$	$dlf/dT$	(3.3)	Amps/ $^\circ\text{C}$
Nonrepetitive Peak Surge Current, $t_p = 8.3$ ms, half-sinewave	$I_{FSM}$	120	Amps
Peak Repetitive Reverse Surge Current, $t_p = 1\mu\text{s}$ , $f = 1\text{kHz}$	$I_{RRM}$	2	Amp
Junction Temperature Range	$T_j$	-55 to +175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +175	$^\circ\text{C}$
Thermal Resistance, Junction to Case:	$\theta_{JC}$	1.25 1.35	$^\circ\text{C/W}$
		1N6817 1N6817R	



① DIMENSION SHOWN APPLIES PRIOR TO SOLDER FINISH. AFTER SOLDER FINISH DIMENSION MAY VARY

NOTE: UNLESS OTHERWISE SPECIFIED

PAD TOLERANCES		
UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN INCHES		
ROUGHNESS	DECIMAL	ANGULAR
63	.XX $\pm .01$ .XXX $\pm .005$	$\pm 0.5^\circ$

**Mechanical Outline**  
**ThinKey™2**

**1N6817**  
**(MSASC25W100K)**

**1N6817R**  
**(MSASC25W100KR)**

**Electrical Parameters**

DESCRIPTION	SYMBOL	CONDITIONS	MIN	TYP.	MAX	UNIT
Reverse (Leakage) Current	IR <sub>25</sub>	VR= 100 Vdc, Tc= 25°C		7	300	μA
	IR <sub>125</sub>	VR= 100 Vdc, Tc= 125°C		2.5	15	mA
Forward Voltage pulse test, pw= 300 μs d/c ≤ 2%	VF1	IF= 5A, Tc= 25°C		650	725	mV
	VF2	IF= 10A, Tc= 25°C		730	810	mV
	VF3	IF= 20A, Tc= 25°C		810	900	mV
	VF4	IF= 50A, Tc= 25°C		940	1020	mV
	VF7	IF= 100A, TC= 25°C		1060	-	mV
	VF5	IF= 20A, Tc= -55°C		925	1025	mV
	VF6	IF= 20A, Tc= 125°C		670	800	mV
Junction Capacitance	Cj1	VR= 10 Vdc		370	500	pF
	Cj2	VR= 5 Vdc		500		pF
Breakdown Voltage	BVR	IR= 1 mA, Tc= 25°C	100	120		V
		IR= 1 mA, Tc= -55°C	100			V



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